Small Signal MOSFET

20 V, 200 mA / -180 mA, Complementary, 1.0 x 1.0 mm SOT-963 Package

Features

- Complementary MOSFET Device
- 1.5 V Gate Voltage Rating
- Ultra Thin Profile (< 0.5 mm) Allows It to Fit Easily into Extremely Thin Environments such as Portable Electronics.
- These are Pb-Free Devices

Applications

- Load Switch with Level Shift
- Optimized for Power Management in Ultra Portable Equipment

MAXIMUM RATINGS (T_J = 25°C unless otherwise specified)

Para	Symbol	Value	Unit			
Drain-to-Source Voltage	V_{DSS}	20	V			
Gate-to-Source Voltag	V _{GS}	±8	V			
N-Channel Continuous Drain	Steady	$T_A = 25^{\circ}C$		160		
Current (Note 1)	State	$T_A = 85^{\circ}C$		115		
	t ≤ 5 s	$T_A = 25^{\circ}C$	ID			
P-Channel	Steady	T _A = 25°C	'D	-140	mA	
Continuous Drain Current (Note 1)	State	T _A = 85°C		-100		
	t ≤ 5 s	$T_A = 25^{\circ}C$		-180		
Power Dissipation (Note 1)	Steady State	T _A = 25°C	P _D	125	mW	
(14010-1)						
	t ≤ 5 s			200		
Pulsed Drain Current	N-Channel	t = 10 us	l	800	mA	
	P-Channel	t _p = 10 μs	I _{DM}	-600	ША	
Operating Junction and	T _J , T _{STG}	–55 to 150	°C			
Source Current (Body I	Is	200	mA			
	Lead Temperature for Soldering Purposes (1/8" from case for 10 s)					

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz. Cu.
- 2. Pulse Test: pulse width \leq 300 μ s, duty cycle \leq 2%

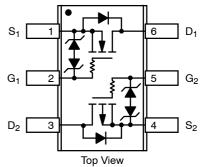


ON Semiconductor®

http://onsemi.com

V _{(BR)DSS}	R _{DS(on)} Max	I _D Max	
	5.0 Ω @ -4.5 V		
P-Channel	7.0 Ω @ -2.5 V	-0.18 A	
–20 V	10 Ω @ -1.8 V	-0.18 A	
	14 Ω @ -1.5 V		
	3.0 Ω @ 4.5 V		
N-Channel 20 V	4.0 Ω @ 2.5 V	0.20 A	
	6.0 Ω @ 1.8 V	0.20 A	
	10 Ω @ 1.5 V		

PINOUT: SOT-963





SOT-963 CASE 527AA



SM

S = Specific Device Code

M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
NTUD3127CT5G	SOT-963 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State, Minimum Pad (Note 3)	$R_{ hetaJA}$	1000	°C/W
$Junction-to-Ambient - t \le 5 s \text{ (Note 3)}$		600	

^{3.} Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz. Cu.

ELECTRICAL CHARACTERISTICS (T₁ = 25°C unless otherwise specified)

Parameter	Symbol	N/P	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS								
Drain-to-Source Breakdown Voltage	.,	N	., .,	I _D = 250 μA	20			.,
	V _{(BR)DSS}	Р	$V_{GS} = 0 V$	I _D = -250 μA	-20			V
Zero Gate Voltage Drain Current			., .,,, -,,,	T _J = 25°C			50	50
		N	$V_{GS} = 0 \text{ V}, V_{DS} = 5.0 \text{ V}$	T _J = 85°C			200	
	I _{DSS}		P $V_{C0} = 0 \text{ V } V_{D0} = -5.0 \text{ V}$	T _J = 25°C			-50	nA
		P		T _J = 85°C			-200	
Zero Gate Voltage Drain Current		N	V _{GS} = 0 V, V _{DS} = 16 V	T 0500			100	
	I _{DSS}	Р	V _{GS} = 0 V, V _{DS} = -16 V	$T_J = 25^{\circ}C$			-100	nA
Gate-to-Source Leakage Current		N	., .,	.5.01/			100	
	I _{GSS}	Р	$V_{DS} = 0 V, V_{GS} =$	±5.0 V			-100	nA
ON CHARACTERISTICS (Note 4)								
Gate Threshold Voltage	.,	N	$V_{GS} = V_{DS}$	I _D = 250 μA	0.4		1.0	V
	V _{GS(TH)}	Р		I _D = -250 μA	-0.4		-1.0	
Drain-to-Source On Resistance		N	V _{GS} = 4.5 V, I _D = 100 mA			1.5	3.0	
		Р	$V_{GS} = -4.5V$, $I_D = -100 \text{ mA}$			4.0	5.0	Ω
		N	V _{GS} = 2.5 V, I _D = 50 mA			2.0	4.0	
		Р	$V_{GS} = -2.5V$, $I_D = -50$ mA			5.0	7.0	
		N	V _{GS} = 1.8 V, I _D = 20 mA			3.0	6.0	
	R _{DS(on)}	Р	$V_{GS} = -1.8V, I_D = -20 \text{ mA}$			6.5	10	
		N	V _{GS} = 1.5 V, I _D = 10 mA			4.0	10	
		Р	$V_{GS} = -1.5 \text{ V}, I_D = -10 \text{ mA}$			7.5	14	
		N	V _{GS} = 1.2 V, I _D = 1.0 mA			5.5		
		Р	$V_{GS} = -1.2 \text{ V}, I_D = -1.2 \text{ V}$	-1.0 mA		11.5		
Forward Transconductance	_	N	V _{DS} = 5.0 V, I _D = 125 mA			0.35		
	9FS	Р	$V_{DS} = -5.0 \text{ V}, I_D = -125 \text{ mA}$			0.26		S
CHARGES, CAPACITANCES AND GA	TE RESISTA	NCE						
Input Capacitance	C _{ISS}					9.0		
Output Capacitance	C _{OSS}	N	f = 1 MHz, V _{GS} = 0 V V _{DS} = 15 V			3.0		
Reverse Transfer Capacitance	C _{RSS}	1				2.2		~_
Input Capacitance	C _{ISS}					12		pF
Output Capacitance	C _{OSS}	Р	f = 1 MHz, V _{GS} : V _{DS} = -15 \	= 0 V /		2.7		7
Reverse Transfer Capacitance	C _{RSS}		VDS = -10 V			1.0		1

^{4.} Switching characteristics are independent of operating junction temperatures

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	N/P	Test Condition	on	Min	Тур	Max	Unit
SWITCHING CHARACTERISTICS, V _{GS} = 4.5 V (Note 4)								
Turn-On Delay Time	t _{d(ON)}				15			
Rise Time	t _r	١.,	V _{GS} = 4.5 V, V _{DD} = 10 V,		24			
Turn-Off Delay Time	t _{d(OFF)}	N	$R_G = 2.0 \Omega$			90		
Fall Time	t _f					60		
Turn-On Delay Time	t _{d(ON)}		$V_{GS} = -4.5 \text{ V}, V_{DD} = -15 \text{ V},$ $I_{D} = -180 \text{ mA}, R_{G} = 2.0 \Omega$			20		ns
Rise Time	t _r	P				37		
Turn-Off Delay Time	t _{d(OFF)}	7 "				112		
Fall Time	t _f					97		
DRAIN-SOURCE DIODE CHARACTERISTICS								
Forward Diode Voltage	V	N	V _{GS} = 0 V, I _S = 10 mA	T _J = 25°C		0.60	1.0	\ <i>/</i>
	V _{SD}	Р	$V_{GS} = 0 \text{ V}, I_{S} = -10 \text{ mA}$			-0.65	-1.0	V

^{4.} Switching characteristics are independent of operating junction temperatures

TYPICAL PERFORMANCE CURVES - N-CHANNEL

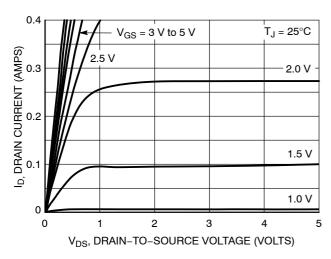


Figure 1. On-Region Characteristics

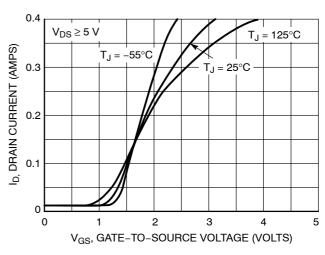


Figure 2. Transfer Characteristics

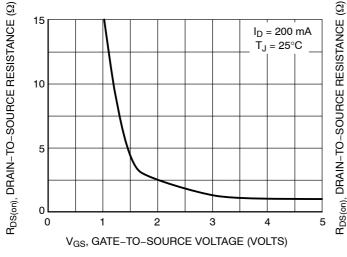


Figure 3. On-Resistance vs. Gate Voltage

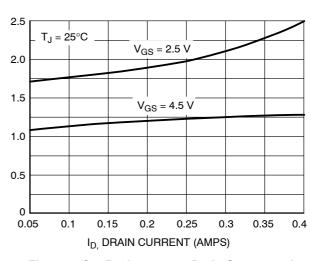


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

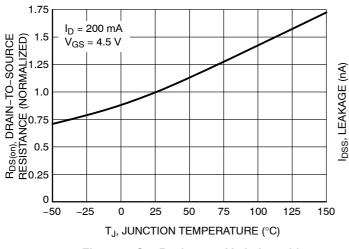


Figure 5. On–Resistance Variation with Temperature

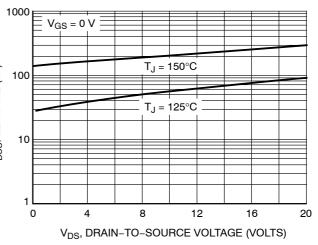


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES - N-CHANNEL

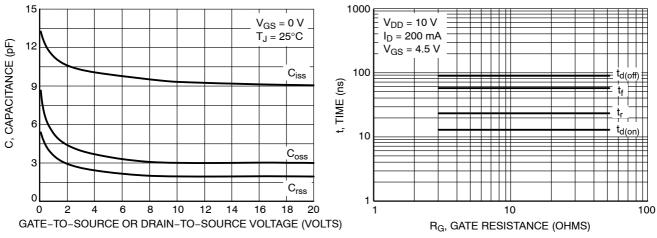


Figure 7. Capacitance Variation

Figure 8. Resistive Switching Time Variation vs. Gate Resistance

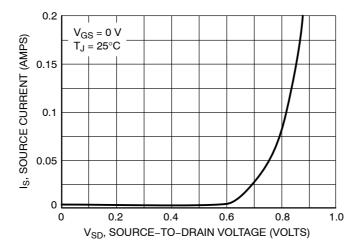


Figure 9. Diode Forward Voltage vs. Current

TYPICAL PERFORMANCE CURVES - P-CHANNEL

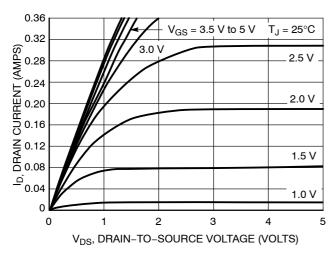


Figure 10. On-Region Characteristics

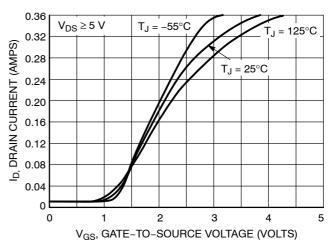


Figure 11. Transfer Characteristics

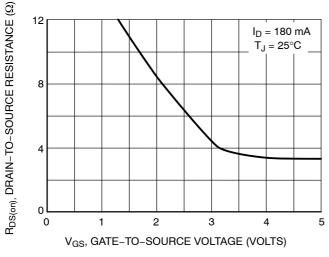


Figure 12. On-Resistance vs. Gate Voltage

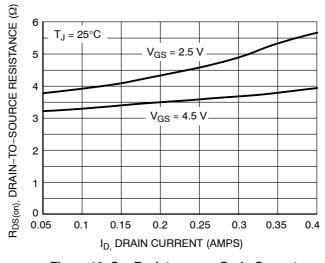


Figure 13. On-Resistance vs. Drain Current and Gate Voltage

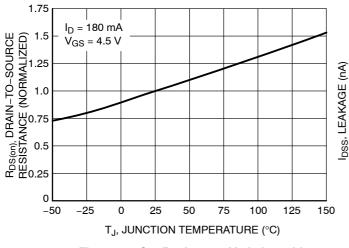


Figure 14. On–Resistance Variation with Temperature

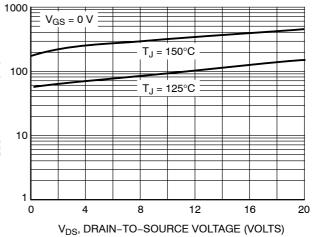


Figure 15. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES - P-CHANNEL

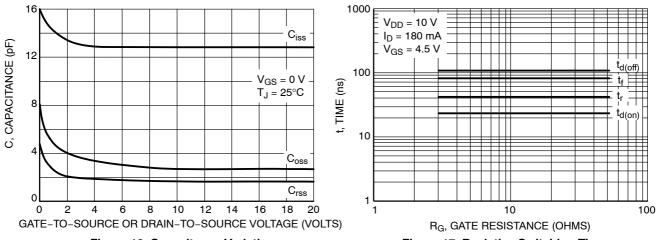


Figure 16. Capacitance Variation

Figure 17. Resistive Switching Time Variation vs. Gate Resistance

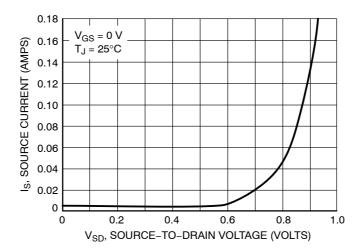
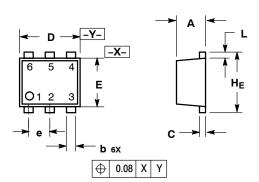


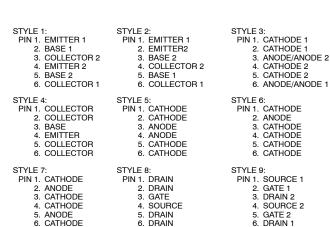
Figure 18. Diode Forward Voltage vs. Current





DATE 30 JUL 2008





NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL

	MII	LIMETE	RS		INCHES			
DIM	MIN	NOM	MAX	MIN	MOM	MAX		
Α	0.40	0.45	0.50	0.016	0.018	0.020		
b	0.10	0.15	0.20	0.004	0.006	0.008		
С	0.05	0.10	0.15	0.002	0.004	0.006		
D	0.95	1.00	1.05	0.037	0.039	0.041		
Е	0.75	0.80	0.85	0.03	0.032	0.034		
е		0.35 BS	С	(0.014 BS	C		
L	0.05	0.10	0.15	0.002	0.004	0.006		
Hε	0.95	1.00	1.05	0.037	0.039	0.041		

GENERIC MARKING DIAGRAM*



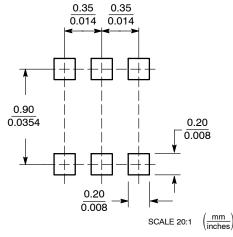
X = Specific Device Code

= Month Code Μ

*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON18698D	Electronic versions are uncontrolled except when accessed directly from the Document Rep Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SOT-963, 1X1, 0.35P		PAGE 1 OF 1		

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